# Power LDMOS transistor Rev. 1 — 16 December 2024

**AMPLEON** 

Product data sheet

#### **Product profile** 1.

## 1.1 General description

A 170 W LDMOS transistor for broadcast, avionics and non-cellular communication applications. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications in the frequency range from HF to 1400 MHz.

Table 1. **Application information** 

Test signal	f	V <sub>DS</sub>	$P_L$	Gp	ησ
	(MHz)	(V)	(W)	(dB)	(%)
pulsed CW	700	50	170	23.8	73

## 1.2 Features and benefits

- Designed for broadband operation
- High efficiency
- Integrated dual sided ESD protection
- Excellent ruggedness
- High power gain
- Excellent reliability
- Easy power control
- Excellent stability
- For RoHS compliance see the product details on the Ampleon website

# 1.3 Applications

- Broadcast transmitter applications
- Avionics applications up to 1400 MHz
- Non-cellular communication applications

#### **Power LDMOS transistor**

# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain	7	
2	gate		1 
3	source	[1] 3[] [] [] [] [] [] [] [] [] [] [] [] [] [	2 -
			3 sym112

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC	J 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	Min. orderable quantity (pieces)
TO-270-2F-1	BLP981Z	934961024515	TR13; 500-fold; 24 mm; dry pack	500
	BLP981XY	934961024538	TR7; 100-fold; 24 mm; dry pack	100

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	108	V
$V_{GS}$	gate-source voltage		-6	+11	٧
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	T <sub>case</sub> = 60 °C; V <sub>DS</sub> = 50 V; P <sub>L</sub> = 170 W	0.50	K/W

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# 6. Characteristics

Table 6. DC characteristics

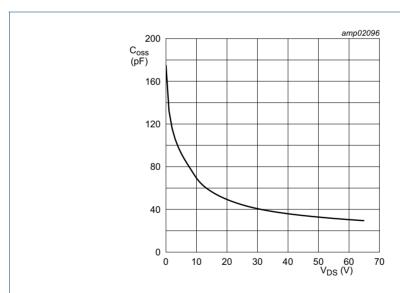
 $T_i$  = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.11 \text{ mA}$	108	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 111 mA	1.5	2.0	2.5	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 25 \text{ mA}$	1.5	1.9	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	20	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.885 \text{ A}$	-	0.19	-	Ω

Table 7. AC characteristics

 $T_i$  = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>rs</sub>	feedback capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	0.79	-	pF
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	111	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	32.8	-	pF



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig 1. Output capacitance as a function of drain-source voltage; typical values per section

#### **Power LDMOS transistor**

Table 8. RF characteristics

Test signal: pulsed CW;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; f = 700 MHz; RF performance at  $V_{DS}$  = 50 V;  $I_{Dq}$  = 25 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

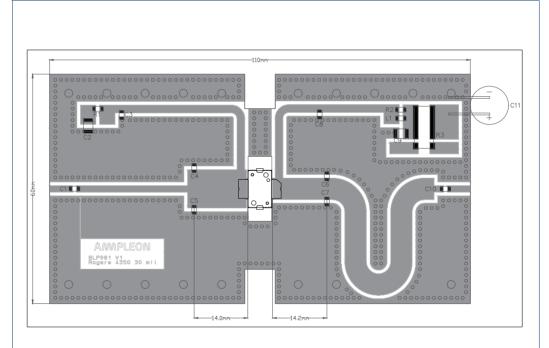
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L</sub> = 170 W	22.5	23.8	-	dB
RLin	input return loss	P <sub>L</sub> = 170 W	-	-12	-9	dB
$\eta_{D}$	drain efficiency	P <sub>L</sub> = 170 W	69	73	-	%

# 7. Test information

## 7.1 Ruggedness in class-AB operation

The BLP981 is capable of withstanding a load mismatch corresponding to VSWR = 40 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{dq}$  = 50 mA;  $P_{L}$  = 170 W; f = 700 MHz; pulsed CW ( $t_{p}$  = 100  $\mu$ s;  $\delta$  = 10 %).

## 7.2 Test circuit



Printed-Circuit Board (PCB): Rogers RO4350B; thickness = 0.762 mm. See  $\underline{\text{Table 9}}$  for a list of components.

Fig 2. Component layout for class-AB production test circuit

#### **Power LDMOS transistor**

Table 9. List of components For test circuit see Figure 2

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	10 pF	[1] [2]
C3	multilayer ceramic chip capacitor	30 pF	[1] [2]
C4, C5	multilayer ceramic chip capacitor	22 pF	[1] [2]
C6, C7	multilayer ceramic chip capacitor	16 pF	[1] [2]
C8	multilayer ceramic chip capacitor	47 pF	[1] [2]
C10	multilayer ceramic chip capacitor	30 pF	[1] [2]
C2, C9	multilayer ceramic chip capacitor	4.7 μF	100 V
C11	electrolytic capacitor	470 μF	64 V
R1	chip resistor	9.1 Ω	SMD 1206
R2	chip resistor	4.7 Ω	SMD 1206
R3	shunt resistor	10 mΩ	
L1	inductor	9 nH	Coilcraft 1508-9N0GLB

- [1] American Technical Ceramics type 800A or capacitor of same quality
- [2] Vertical mounted

## 7.3 Graphical data

## 7.3.1 Pulsed CW performance measured in production RF test circuit

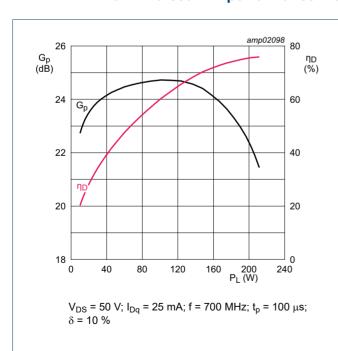
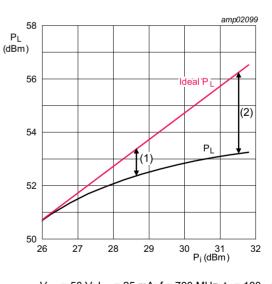


Fig 3. Power gain and drain efficiency as a function of output power; typical values

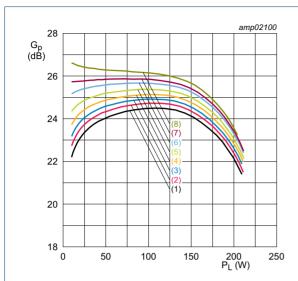


 $V_{DS}$  = 50 V;  $I_{Dq}$  = 25 mA; f = 700 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %

- (1)  $P_{L(1 dB)} = 52.4 dBm (172 W)$
- (2)  $P_{L(3 dB)} = 53.2 dBm (208 W)$

Fig 4. Output power as a function of input power; typical values

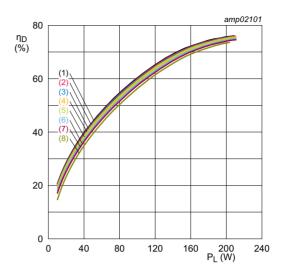
#### **Power LDMOS transistor**



 $V_{DS}$  = 50 V; f = 700 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %

- (1)  $I_{Dq} = 10 \text{ mA}$
- (2)  $I_{Dq} = 25 \text{ mA}$
- (3)  $I_{Dq} = 50 \text{ mA}$
- (4)  $I_{Dq} = 100 \text{ mA}$
- (5)  $I_{Dq} = 200 \text{ mA}$
- (6)  $I_{Dq} = 400 \text{ mA}$
- (7)  $I_{Dq} = 600 \text{ mA}$
- (8)  $I_{Dq} = 1000 \text{ mA}$

Fig 5. Power gain as a function of output power; typical values

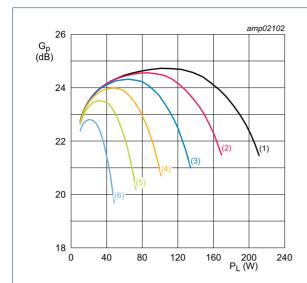


 $V_{DS}$  = 50 V; f = 700 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %

- (1)  $I_{Dq} = 10 \text{ mA}$
- (2)  $I_{Dq} = 25 \text{ mA}$
- (3)  $I_{Dq} = 50 \text{ mA}$
- (4)  $I_{Dq} = 100 \text{ mA}$
- (5)  $I_{Dq} = 200 \text{ mA}$
- (6)  $I_{Dq} = 400 \text{ mA}$
- (7)  $I_{Dq} = 600 \text{ mA}$
- (8)  $I_{Dq} = 1000 \text{ mA}$

Fig 6. Drain efficiency as a function of output power; typical values

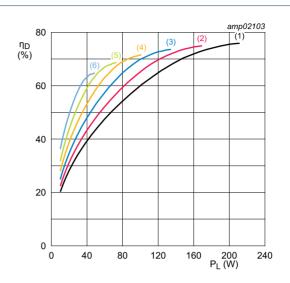
#### **Power LDMOS transistor**



 $I_{Dq}$  = 25 mA; f = 700 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %

- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 \text{ V}$
- (5)  $V_{DS} = 30 \text{ V}$
- (6)  $V_{DS} = 25 \text{ V}$

Fig 7. Power gain as a function of output power; typical values

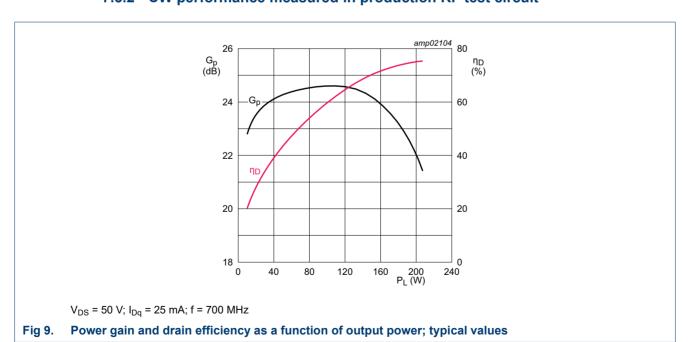


 $I_{Dq}$  = 25 mA; f = 700 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %

- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 V$
- (5)  $V_{DS} = 30 \text{ V}$
- (6)  $V_{DS} = 25 V$

Fig 8. Drain efficiency as a function of output power; typical values

# 7.3.2 CW performance measured in production RF test circuit



#### **Power LDMOS transistor**

# 8. Package outline

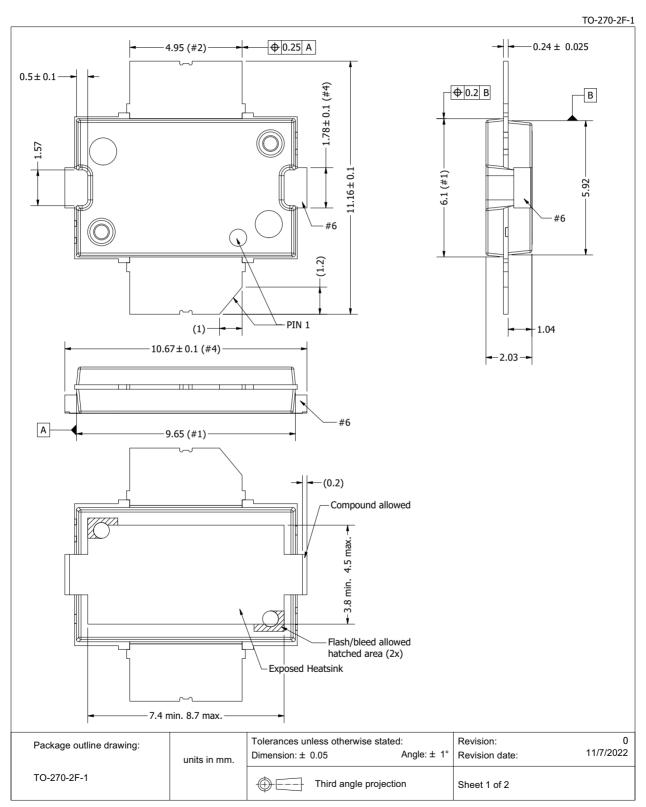


Fig 10. Package outline TO-270-2F-1 (sheet 1 of 2)

#### **Power LDMOS transistor**

TO-270-2F-1

	Drawing Notes
Items	Description
(1)	Dimensions are excluding mold protrusion. The mold protrusion is maximum 0.15 mm per side. See also detail B.
(1)	In the dambar area max. protrusion is 0.55 mm. max. in length and 0.3 mm. max. in width (4x). See also detail B.
(2)	The lead dambar (metal) protrusions are not included. Add 0.14 mm max to the total lead dimension at the dambar location.
(3)	The leads and exposed heatsink are plated with matte Tin (Sn).
(4)	Dimensions (Heatsink ears) 10,67 and 1,78 do not include mouldprotrusion. Overall Max. dimensions incl. mould
(4)	protrusions is 10.92 mm. (max.) and 2.03 mm. (max.).
(5)	Lead coplanarity over the leads is 0,1 mm. maximum.
(6)	Surfaces may remain unplated (not solderable surfaces).

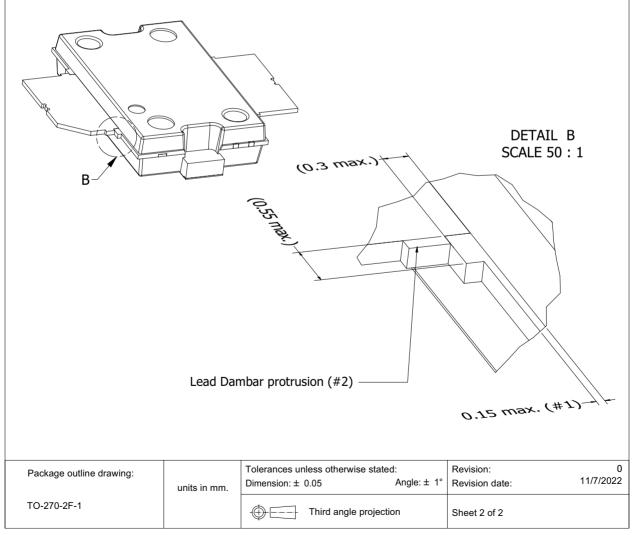


Fig 11. Package outline TO-270-2F-1 (sheet 2 of 2)

**Power LDMOS transistor** 

# 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 10. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2B [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2B is granted to any part that passes after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

## 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CW	Continuous Wave
DVB-T	Digital Video Broadcast - Terrestrial
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
RoHS	Restriction of Hazardous Substances
VSWR	Voltage Standing Wave Ratio

# 11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP981 v1	20241216	Production data sheet	-	-

#### **Power LDMOS transistor**

# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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